

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

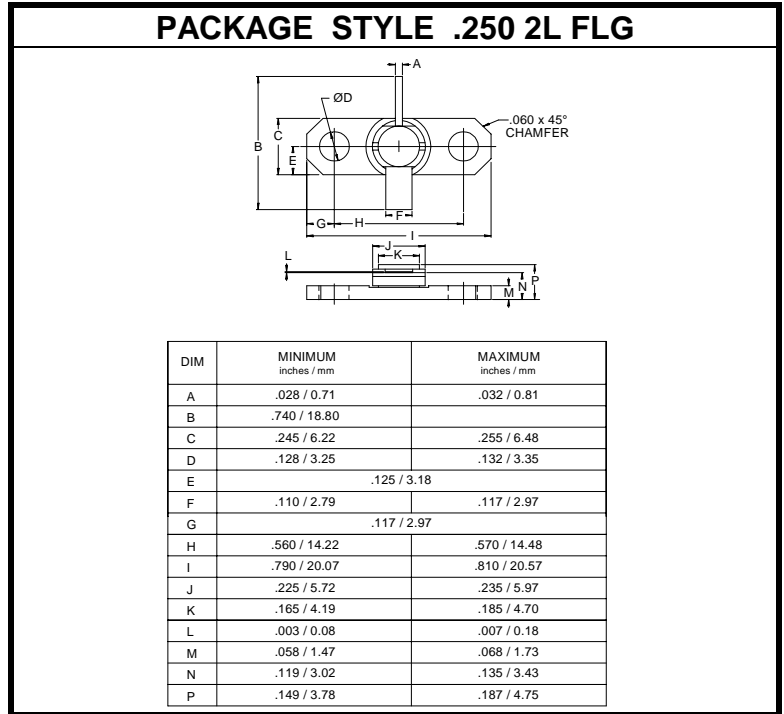
The **ASI PTB32001X** is Designed for Common Base General purpose amplifier Applications up to 4.2 GHz.

**FEATURES INCLUDE:**

- Diffused Emitter Ballasting Resistor
- Hermetic Flange Package
- Gold Metelization

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	250 mA
<b>V<sub>CB0</sub></b>	40 V
<b>P<sub>DISS</sub></b>	4.2 W @ T <sub>C</sub> = 75 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +200 °C
<b>θ<sub>JC</sub></b>	22 °C/W


**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CB0</sub></b>	I <sub>C</sub> = 1.0 mA			40			V
<b>BV<sub>CES</sub></b>	I <sub>C</sub> = 10 mA			40			V
<b>I<sub>CB0</sub></b>	V <sub>CE</sub> = 24 V					10	µA
<b>I<sub>EBO</sub></b>	V <sub>EB</sub> = 1.5 V					0.2	µA
<b>C<sub>cb</sub></b>	V <sub>CB</sub> = 24 V	V <sub>EB</sub> = 1.5 V	f = 1.0 MHz		2.2		pF
<b>C<sub>ce</sub></b>	V <sub>CB</sub> = 24 V	V <sub>EB</sub> = 1.5 V	f = 1.0 MHz		0.3		pF
<b>P<sub>OUT</sub></b>	V <sub>CC</sub> = 24 V      f = 3.0 GHz			1.3			W
<b>η<sub>C</sub></b>				35			%
<b>G<sub>P</sub></b>				8.0			dB